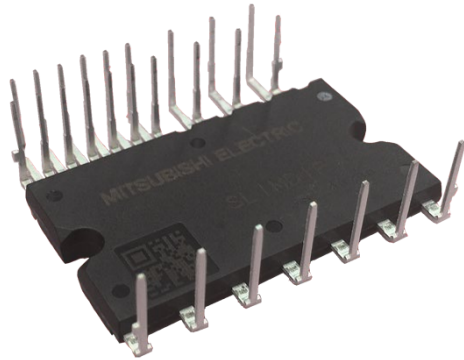


< DIIPM >

SLIMDIP-W

TRANSFER MOLDING TYPE
INSULATED TYPE

OUTLINE



Normal terminal type

MAIN FUNCTION AND RATINGS

- RC-IGBT inverter bridge for three phase DC-to-AC power conversion
- Built-in bootstrap diodes with current limiting resistor
- Open emitter type

APPLICATION

- AC 100~240V (DC voltage:400V or below) three phase low power motor inverter drive

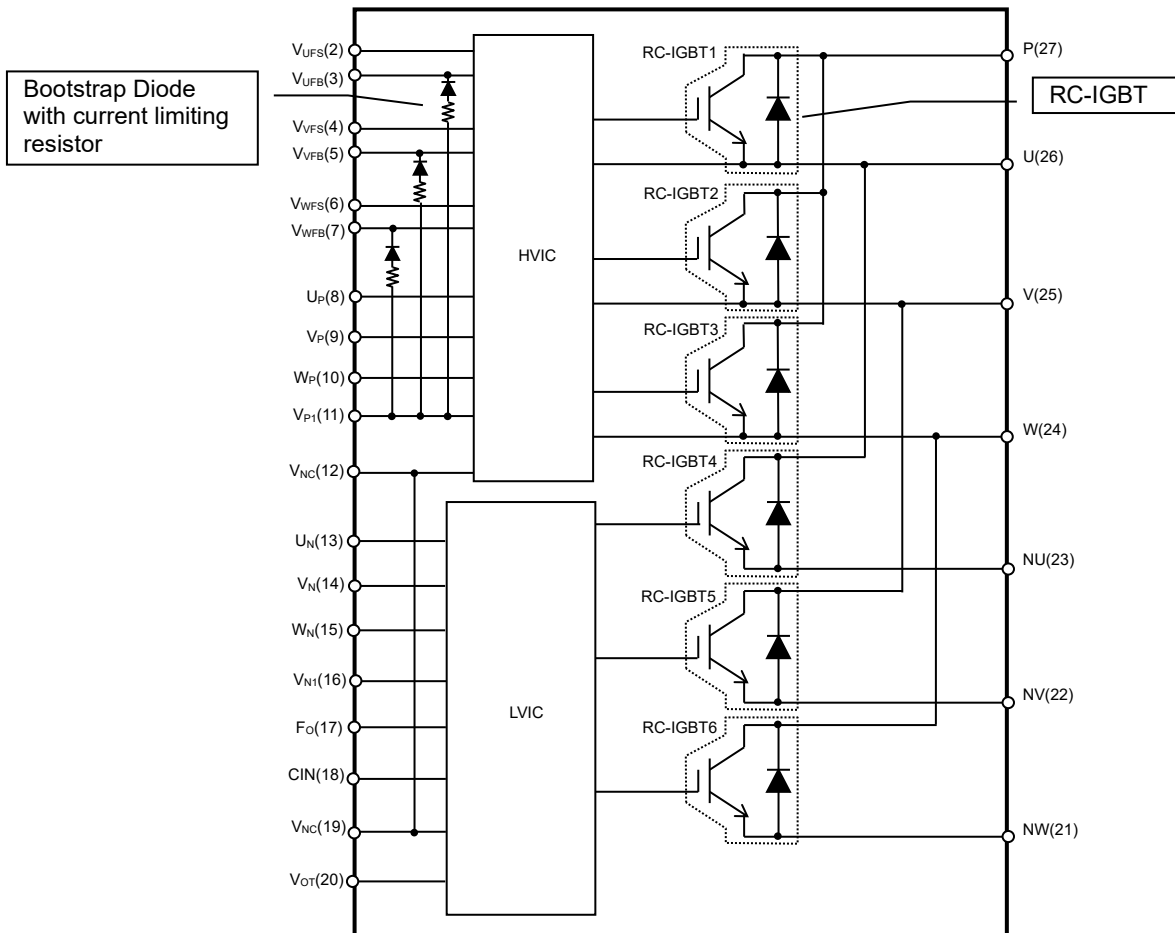
TERMINAL LINE UP

Terminal	Part number	Suffix
Normal terminal	SLIMDIP-W	500
Short terminal	SLIMDIP-W	505

INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS

- For P-side : Drive circuit, High voltage high-speed level shifting, Control supply under-voltage protection (UV)
- For N-side : Drive circuit, Control supply under-voltage protection (UV), Short circuit protection (SC), Over temperature protection (OT)
- Fault signaling : Corresponding to SC fault (N-side IGBT), UV fault (N-side supply) and OT fault
- Temperature monitoring : Outputting LVIC temperature by analog signal
- Input interface : Schmitt-triggered 3V, 5V input compatible, high active logic.
- UL Recognized : UL1557 File E323585

INTERNAL CIRCUIT



MAXIMUM RATINGS ($T_j = 25^\circ\text{C}$, unless otherwise noted)**INVERTER PART**

Symbol	Parameter	Condition	Ratings	Unit
V_{CC}	Supply voltage	Applied between P-NU, NV, NW	450	V
$V_{CC(\text{surge})}$	Supply voltage (surge)	Applied between P-NU, NV, NW	500	V
V_{CES}	Collector-emitter voltage		600	V
$\pm I_C$	Each IGBT collector current	$T_C = 25^\circ\text{C}$ (Note 1)	15	A
$\pm I_{CP}$	Each IGBT collector current (peak)	$T_C = 25^\circ\text{C}$, less than 1ms	30	A
T_j	Junction temperature	(Note 2)	-30~+150	$^\circ\text{C}$

Note1: Pulse width and period are limited due to junction temperature.

Note2 The maximum junction temperature rating of the power chips integrated within the DIIPM is 150°C (@ $T_C \leq 115^\circ\text{C}$) however, to insure safe operation of the DIIPM, the average junction temperature should be limited to $T_{j(\text{ave})} \leq 125^\circ\text{C}$ (@ $T_C \leq 115^\circ\text{C}$).**CONTROL (PROTECTION) PART**

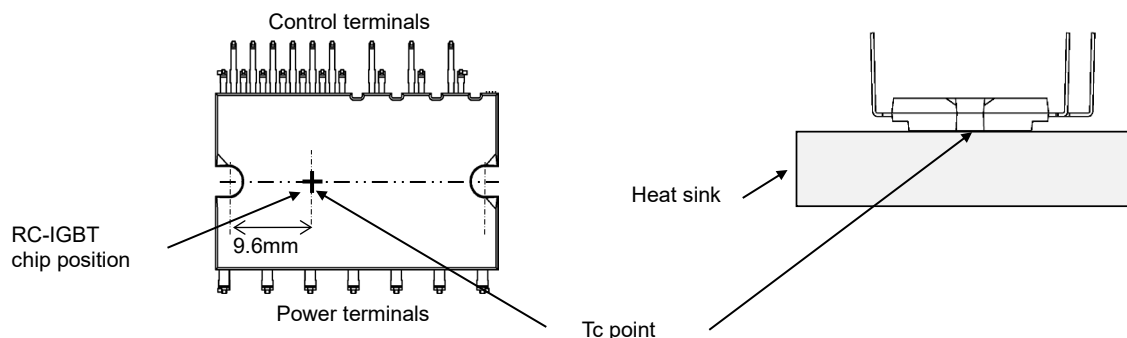
Symbol	Parameter	Condition	Ratings	Unit
V_D	Control supply voltage	Applied between $V_{P1}-V_{NC}$, $V_{N1}-V_{NC}$	20	V
V_{DB}	Control supply voltage	Applied between $V_{UFB}-V_{UFS}$, $V_{VFB}-V_{VFS}$, $V_{WFB}-V_{WFS}$	20	V
V_{IN}	Input voltage	Applied between U_P , V_P , W_P , U_N , V_N , W_N-V_{NC}	-0.5~ $V_D+0.5$	V
V_{FO}	Fault output supply voltage	Applied between F_O-V_{NC}	-0.5~ $V_D+0.5$	V
I_{FO}	Fault output current	Sink current at F_O terminal	1	mA
V_{SC}	Current sensing input voltage	Applied between $CIN-V_{NC}$	-0.5~ $V_D+0.5$	V

TOTAL SYSTEM

Symbol	Parameter	Condition	Ratings	Unit
$V_{CC(\text{PROT})}$	Self protection supply voltage limit (Short circuit protection capability)	$V_D = 13.5\sim 16.5\text{V}$, Inverter Part $T_j = 150^\circ\text{C}$, non-repetitive, less than 2 μs	400	V
T_C	Module case operation temperature	Measurement point of T_C is described in Fig.1 (Note3)	-30~+115	$^\circ\text{C}$
T_{stg}	Storage temperature		-40~+125	$^\circ\text{C}$
V_{iso}	Isolation voltage	60Hz, Sinusoidal, AC 1min, between connected all pins and heat sink plate	2000	V_{rms}

Note3 T_C MEASUREMENT POINT

Fig. 1

**THERMAL RESISTANCE**

Symbol	Parameter	Condition	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Junction to case thermal resistance (Note 4)	Inverter RC-IGBT part (per 1/6 module)	-	-	4.0	K/W

Note 4: Grease with good thermal conductivity and long-term endurance should be applied evenly with about $+100\mu\text{m}\sim+200\mu\text{m}$ on the contacting surface of DIIPM and heat sink. The contacting thermal resistance between DIIPM case and heat sink $R_{th(c-f)}$ is determined by the thickness and the thermal conductivity of the applied grease. For reference, $R_{th(c-f)}$ is about 0.4K/W (per 1/6 module, grease thickness: 20 μm , thermal conductivity: 1.0W/m \cdot K).

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$, unless otherwise noted)**INVERTER PART**

Symbol	Parameter	Condition	Limits			Unit
			Min.	Typ.	Max.	
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_D=V_{DB} = 15\text{V}$, $V_{IN}= 5\text{V}$	-	1.95	2.40	V
		$I_C= 15\text{A}$, $T_j= 25^\circ\text{C}$		2.30	2.75	
V_{EC}	FWDi forward voltage	$V_{IN}= 0\text{V}$, $-I_C= 15\text{A}$	-	1.60	2.20	V
t_{on}	Switching times	$V_{CC}= 300\text{V}$, $V_D= V_{DB}= 15\text{V}$ $I_C= 15\text{A}$, $T_j= 125^\circ\text{C}$, $V_{IN}= 0\sim 5\text{V}$ Inductive Load (upper-lower arm)	0.60	1.00	1.40	μs
$t_{C(on)}$			-	0.35	0.60	μs
t_{off}			-	1.15	1.60	μs
$t_{C(off)}$			-	0.15	0.30	μs
t_{rr}			-	0.20	-	μs
I_{CES}	Collector-emitter cut-off current	$V_{CE}=V_{CES}$	-	-	1	mA
		$T_j= 125^\circ\text{C}$		-	10	

CONTROL (PROTECTION) PART

Symbol	Parameter	Condition	Limits			Unit
			Min.	Typ.	Max.	
I_D	Circuit current	Total of $V_{P1}-V_{NC}$, $V_{N1}-V_{NC}$	-	-	3.10	mA
		$V_D=15\text{V}$, $V_{IN}=0\text{V}$			4.20	
I_{DB}		Each part of $V_{UFB}-V_{UFS}$, $V_{VFB}-V_{VFS}$, $V_{WFB}-V_{WFS}$	-	-	0.10	
		$V_D=V_{DB}=15\text{V}$, $V_{IN}=5\text{V}$			0.10	
$V_{SC(ref)}$	Short circuit trip level	$V_D = 15\text{V}$ (Note 5)	0.455	0.480	0.505	V
UV_{DBt}	P-side Control supply under-voltage protection(UV)	Trip level	9.0	10.0	12.0	V
UV_{DBr}		Reset level	9.0	10.0	12.0	V
UV_{Dt}	N-side Control supply under-voltage protection(UV)	Trip level	10.3	-	12.5	V
UV_{Dr}		Reset level	10.8	-	13.0	V
V_{OT}	Temperature Output	Pull down R=5.1k Ω (Note 6) LVIC Temperature=95 $^\circ\text{C}$	2.76	2.89	3.03	V
OT_t	Over temperature protection (Note 7)	$V_D = 15\text{V}$, Detect LVIC temperature	115	130	145	$^\circ\text{C}$
OT_{rh}		Hysteresis of trip-reset	-	10	-	$^\circ\text{C}$
V_{FOH}	Fault output voltage	$V_{SC} = 0\text{V}$, F_o terminal pulled up to 5V by 10k Ω	4.9	-	-	V
V_{FOL}		$V_{SC} = 1\text{V}$, $I_{FO} = 1\text{mA}$	-	-	0.95	V
t_{FO}	Fault output pulse width	(Note 8)	20	-	-	μs
I_{IN}	Input current	$V_{IN} = 5\text{V}$	0.70	1.00	1.50	mA
$V_{th(on)}$	ON threshold voltage	Applied between U_P , V_P , W_P , U_N , V_N , W_N-V_{NC}	-	1.70	2.35	V
$V_{th(off)}$	OFF threshold voltage		0.70	1.30	-	
$V_{th(hys)}$	ON/OFF threshold hysteresis voltage		0.25	0.40	-	
V_F	Bootstrap Di forward voltage	$I_F=10\text{mA}$ including voltage drop by limiting resistor (Note 9)	1.1	1.7	2.3	V
R	Built-in limiting resistance	Included in bootstrap Di	80	100	120	Ω

Note 5 : SC protection works only for N-side IGBT. Please select the external shunt resistance such that the SC trip-level is less than 1.7 times of the current rating.

6 : Temperature of LVIC vs. V_{OT} output characteristics is described in Fig.3. These minimum and maximum curves are based on theoretical designed value excluding LVIC temperature=95 $^\circ\text{C}$ limits.

7 : When the LVIC temperature exceeds OT trip temperature level(OT_t), OT protection works and F_o outputs. In that case if the heatsink dropped off or fixed loosely, don't reuse that DIIPM. (There is a possibility that junction temperature of power chips exceeded maximum $T_j(150^\circ\text{C})$.)

8 : Fault signal F_o outputs when SC, UV or OT protection works. F_o pulse width is different for each protection modes. At SC failure, F_o pulse width is a fixed width (=minimum 20 μs), but at UV or OT failure, F_o outputs continuously until recovering from UV or OT state. (But minimum F_o pulse width is 20 μs .)

9 : The characteristics of bootstrap Di is described in Fig.2.

Fig. 2 Characteristics of Bootstrap Di V_F - I_F curve (@ $T_a=25^\circ\text{C}$) Including Voltage Drop by Limiting Resistor (Right chart is enlarged chart.)

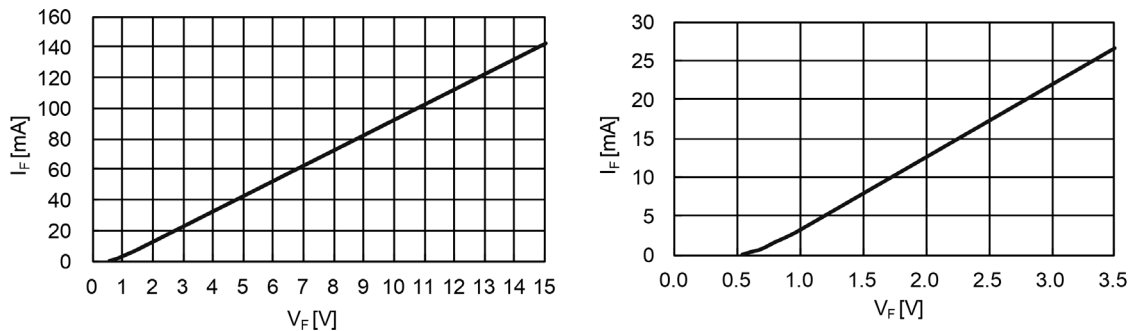
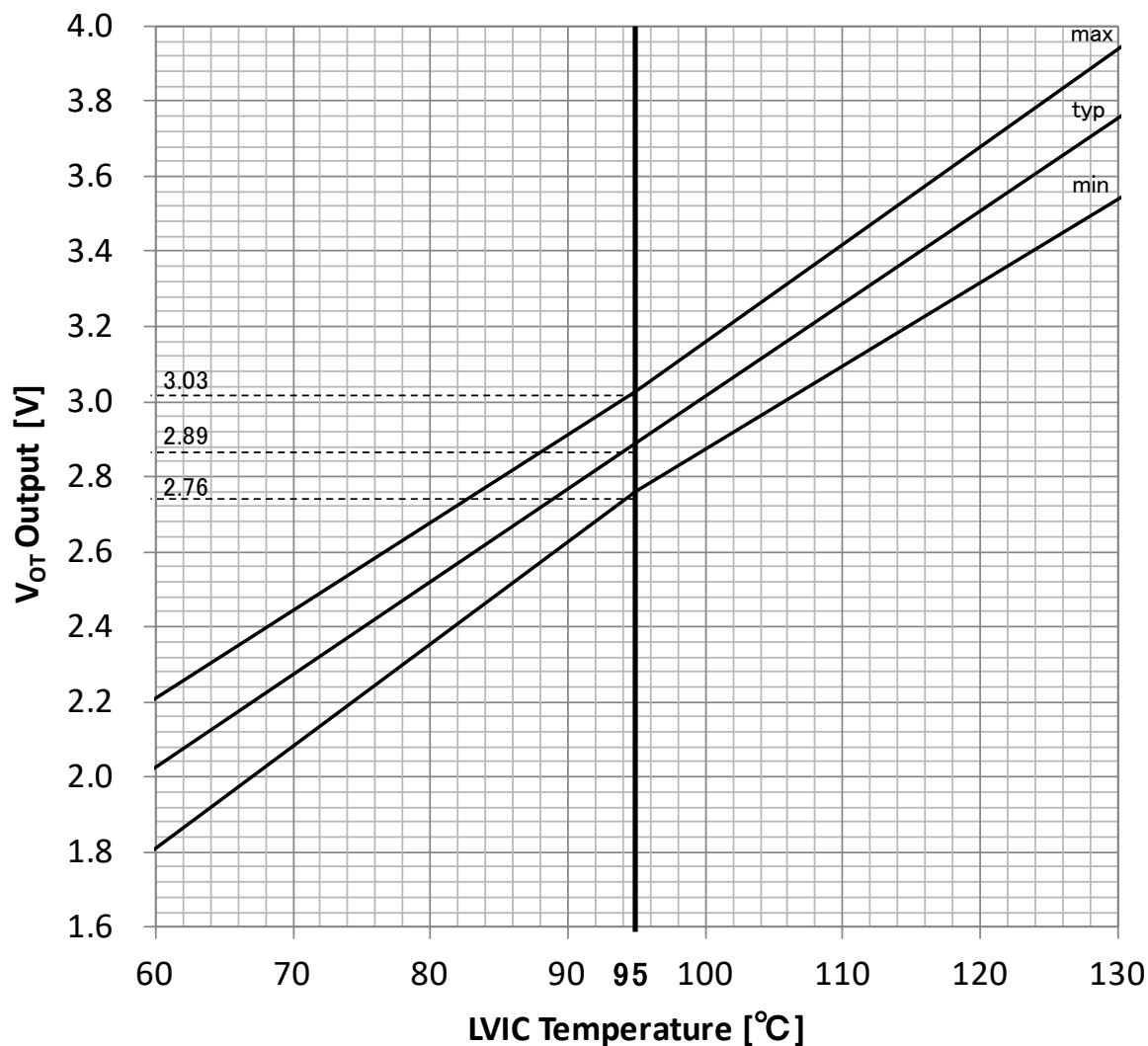
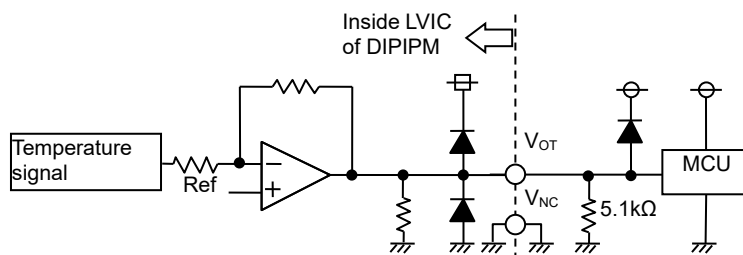


Fig. 3 Temperature of LVIC vs. V_{OT} Output CharacteristicsFig. 4 Pattern Wiring Around the Analog Voltage Output Circuit [V_{OT} terminal]

- (1) V_{OT} outputs the analog signal that is amplified signal of temperature detecting element on LVIC by inverting amplifier.
- (2) It is recommended to insert 5kΩ (5.1kΩ is recommended) pull down resistor for getting linear output characteristics at low temperature below room temperature. When the pull down resistor is inserted between V_{OT} and V_{NC} (control GND), the extra circuit current, which is calculated approximately by V_{OT} output voltage divided by pull down resistance, flows as LVIC circuit current continuously. In the case of using V_{OT} for detecting high temperature over room temperature only, it is unnecessary to insert the pull down resistor.
- (3) In the case of using V_{OT} with low voltage controller like 3.3V MCU, V_{OT} output might exceed control supply voltage 3.3V when temperature rises excessively. If system uses low voltage controller, it is recommended to insert a clamp Di between control supply of the controller and V_{OT} output for preventing over voltage destruction.
- (4) In the case of not using V_{OT} , leave V_{OT} output NC (No Connection).

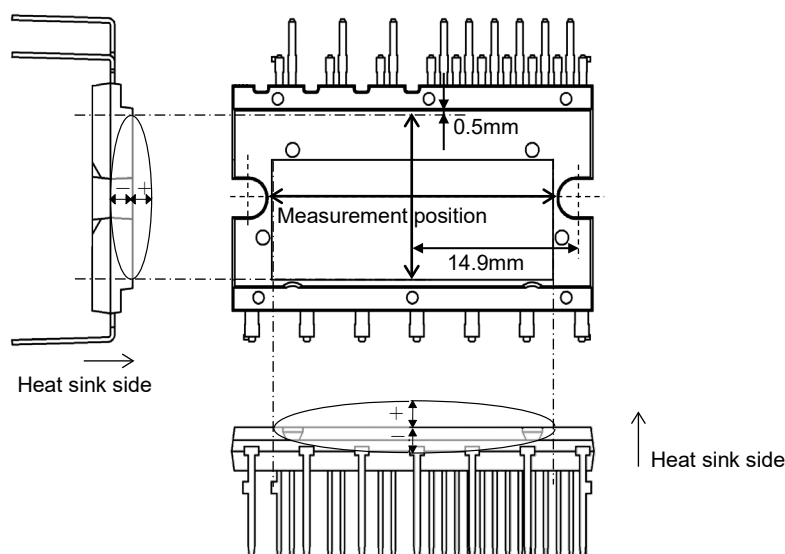
Refer the application note for SLIMDIP series about the usage of V_{OT} .

SLIMDIP-W**TRANSFER MOLDING TYPE
INSULATED TYPE****MECHANICAL CHARACTERISTICS AND RATINGS**

Parameter	Condition	Reference	Limits			Unit
			Min.	Typ.	Max.	
Mounting torque	Mounting screw : M3 (Note 10)	JEITA-ED-4701 402 method II	0.59	0.69	0.78	N·m
Terminal strength pull	Control terminal: Load 5N Power terminal: Load 10N	JEITA-ED-4701 401 method I	10	-	-	s
Terminal strength bending	Control terminal: Load 2.5N Power terminal: Load 5N 90deg. Bend	JEITA-ED-4701 401 method III	2	-	-	times
Weight		-	-	5.5	-	g
Heat radiation part flatness	(Note 11)	-	-30	-	80	μm

Note 10: Plain washers (ISO 7089~7094) are recommended.

Note 11: Measurement positions of heat radiation part flatness are as below

**RECOMMENDED OPERATION CONDITIONS**

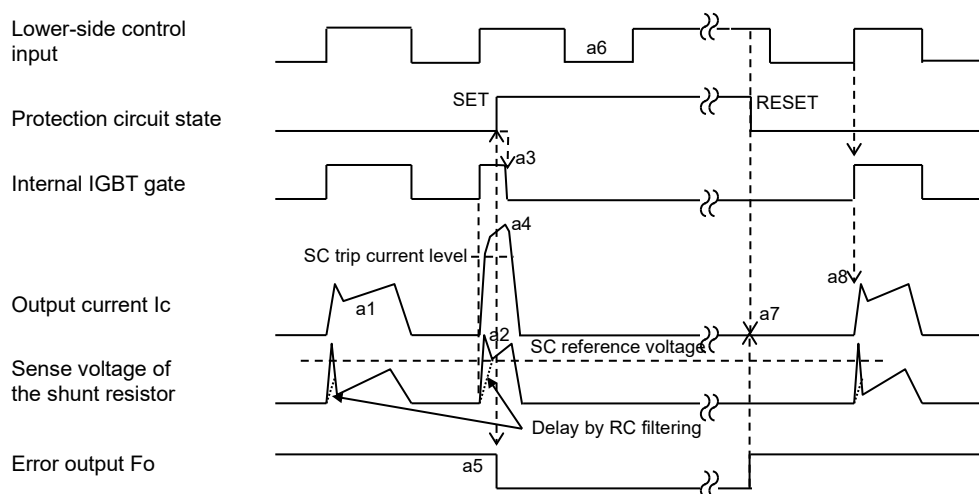
Symbol	Parameter	Condition	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	Supply voltage	Applied between P-NU, NV, NW	0	300	400	V
V_D	Control supply voltage	Applied between V_{P1} - V_{NC} , V_{N1} - V_{NC}	13.5	15.0	16.5	V
V_{DB}	Control supply voltage	Applied between V_{UFB} - V_{UFS} , V_{VFB} - V_{VFS} , V_{WFB} - V_{WFS}	13.0	15.0	18.5	V
ΔV_D , ΔV_{DB}	Control supply variation		-1	-	+1	V/μs
t_{dead}	Arm shoot-through blocking time	For each input signal	1.0	-	-	μs
f_{PWM}	PWM input frequency	$T_C \leq 115^\circ\text{C}$, $T_j \leq 125^\circ\text{C}$	-	-	20	kHz
PWIN(on)	Minimum input pulse width	(Note 12)	0.7	-	-	μs
PWIN(off)			0.7	-	-	
V_{NC}	V_{NC} variation	Between V_{NC} -NU, NV, NW (including surge)	-5.0	-	+5.0	V
T_j	Junction temperature		-20	-	125	°C

Note 12: When inputting shorter pulse than PWIN(on) / PWIN(off), DIIPM might not make response.

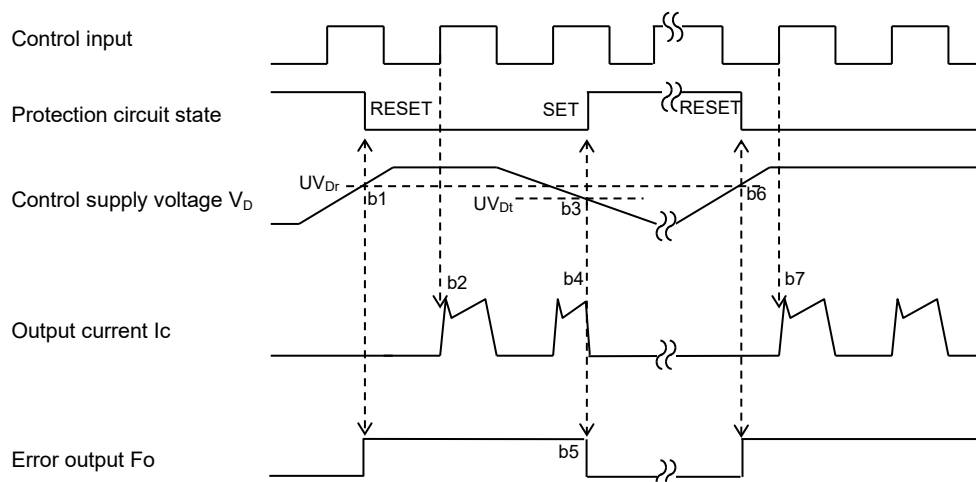
Fig. 5 Timing Charts of The DIIPM Protective Functions

[A] Short-Circuit Protection (N-side only with the external shunt resistor and RC filter)

- a1. Normal operation: IGBT ON and outputs current.
- a2. Short circuit current detection (SC trigger)
(It is recommended to set RC time constant 1.5~2.0 μ s so that IGBT shut down within 2.0 μ s when SC.)
- a3. All N-side IGBT's gates are hard interrupted.
- a4. All N-side IGBTs turn OFF.
- a5. F_o outputs for t_{Fo} =minimum 20 μ s.
- a6. Input = "L": IGBT OFF
- a7. F_o finishes output, but IGBTs don't turn on until inputting next ON signal (L \rightarrow H).
- (IGBT of each phase can return to normal state by inputting ON signal to each phase.)
- a8. Normal operation: IGBT ON and outputs current.

**[B] Under-Voltage Protection (N-side, UV_D)**

- b1. Control supply voltage V_D exceeds under voltage reset level (UV_{Dr}), but IGBT turns ON by next ON signal (L \rightarrow H).
(IGBT of each phase can return to normal state by inputting ON signal to each phase.)
- b2. Normal operation: IGBT ON and outputs current.
- b3. V_D level drops to under voltage trip level. (UV_{Dt}).
- b4. All N-side IGBTs turn OFF in spite of control input condition.
- b5. F_o outputs for t_{Fo} =minimum 20 μ s, but output is extended during V_D keeps below UV_{Dr} .
- b6. V_D level reaches UV_{Dr} .
- b7. Normal operation: IGBT ON and outputs current.

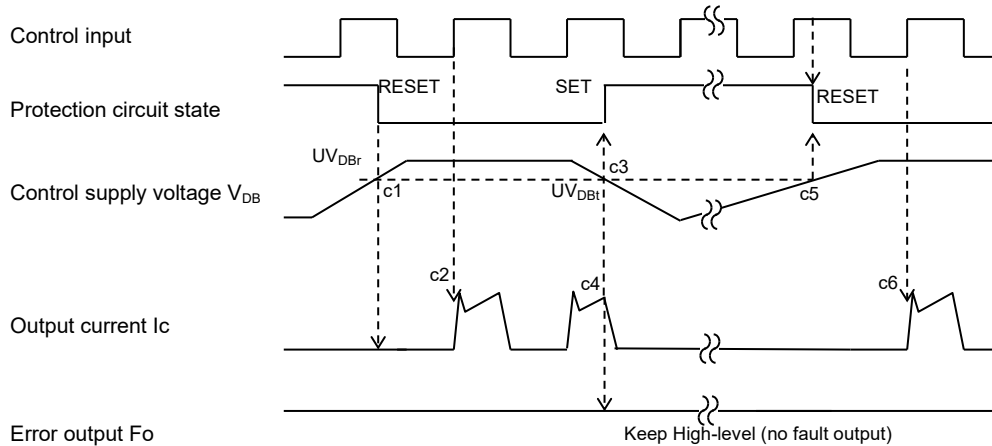


SLIMDIP-W

TRANSFER MOLDING TYPE
INSULATED TYPE

[C] Under-Voltage Protection (P-side, UV_{DB})

- c1. Control supply voltage V_{DB} rises. After the voltage reaches under voltage reset level UV_{DBr} , IGBT turns on by next ON signal (L→H).
 c2. Normal operation: IGBT ON and outputs current.
 c3. V_{DB} level drops to under voltage trip level (UV_{DBt}).
 c4. IGBT of the corresponding phase only turns OFF in spite of control input signal level, but there is no F_o signal output.
 c5. V_{DB} level reaches UV_{DBr} .
 c6. Normal operation: IGBT ON and outputs current.

**[D] Over Temperature Protection (N-side, Detecting LVIC temperature)**

- d1. Normal operation: IGBT ON and outputs current.
 d2. LVIC temperature exceeds over temperature trip level (OT_t).
 d3. All N-side IGBTs turn OFF in spite of control input condition.
 d4. F_o outputs for t_{Fo} =minimum $20\mu s$, but output is extended during LVIC temperature keeps over OT_t .
 d5. LVIC temperature drops to over temperature reset level.
 d6. Normal operation: IGBT turns on by next ON signal (L→H).
 (IGBT of each phase can return to normal state by inputting ON signal to each phase.)

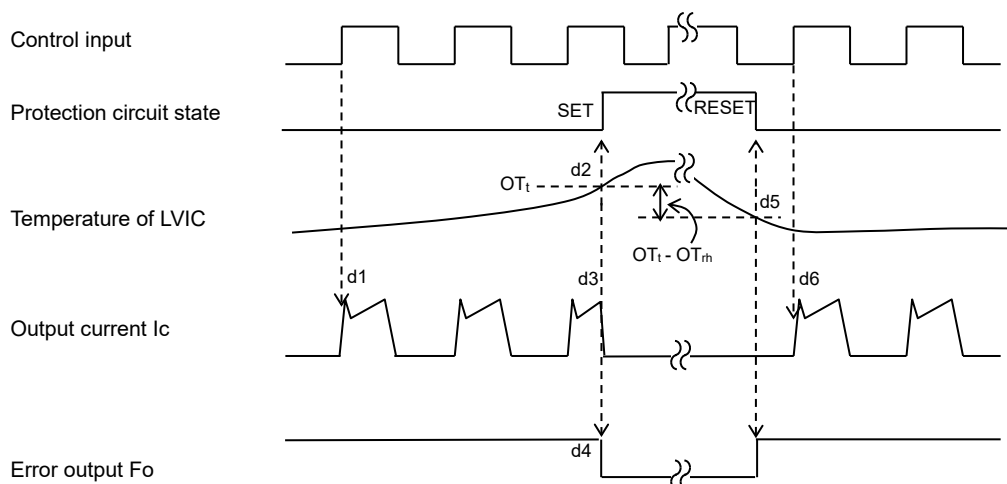
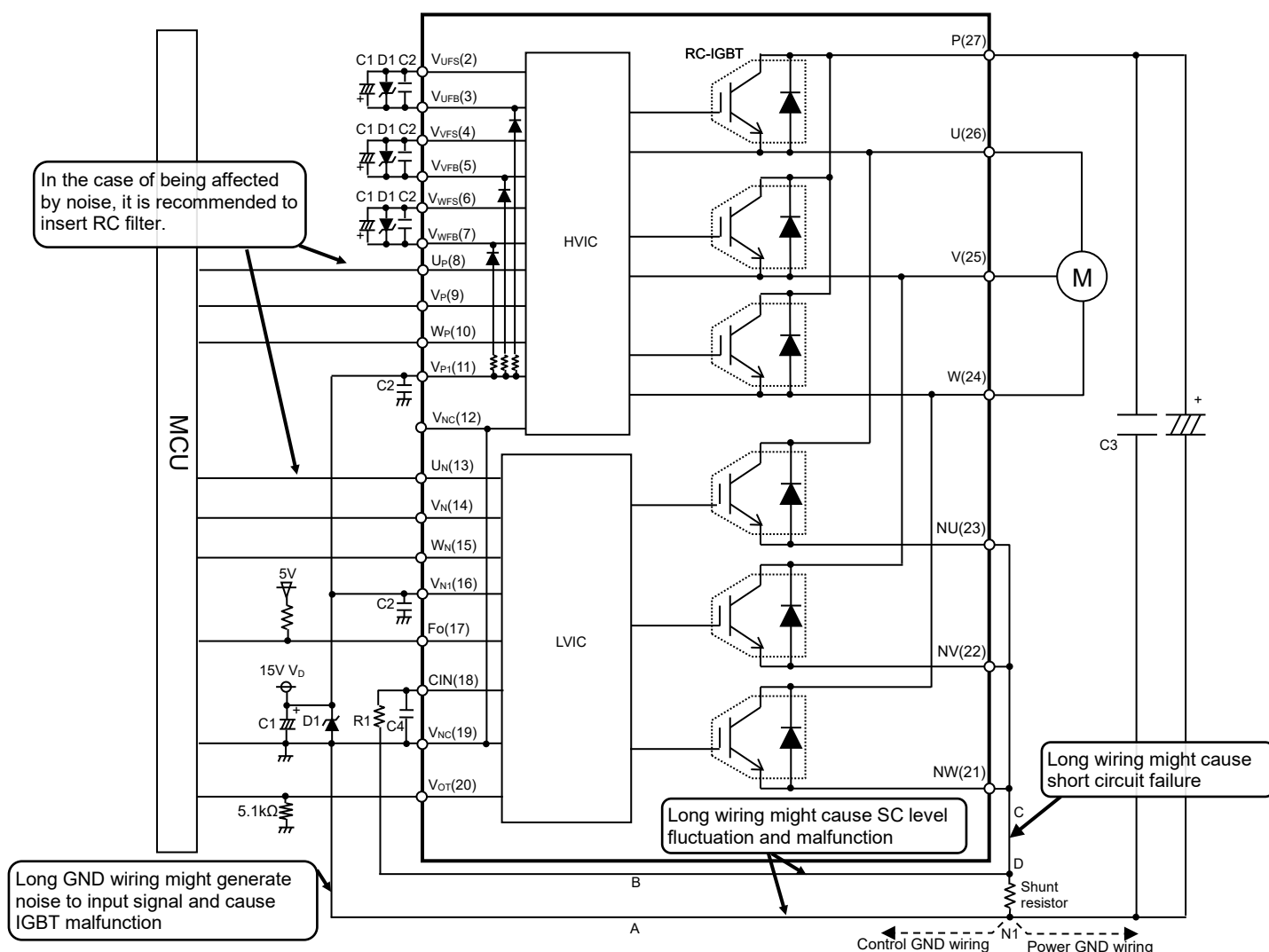


Fig. 6 Example of Application Circuit



- (1) If control GND is connected with power GND by common broad pattern, it may cause malfunction by power GND fluctuation. It is recommended to connect control GND and power GND at only a point N1 (near the terminal of shunt resistor).
- (2) It is recommended to insert a Zener diode D1(24V/1W) between each pair of control supply terminals to prevent surge destruction.
- (3) To prevent surge destruction, the wiring between the smoothing capacitor and the P, N1 terminals should be as short as possible. Generally a 0.1-0.22 μ F snubber capacitor C3 between the P-N1 terminals is recommended.
- (4) R1, C4 of RC filter for preventing protection circuit malfunction is recommended to select tight tolerance, temp-compensated type. The time constant R1C4 should be set so that SC current is shut down within 2 μ s. (1.5 μ s~2 μ s is general value.) SC interrupting time might vary with the wiring pattern, so the enough evaluation on the real system is necessary.
- (5) To prevent malfunction, the wiring of A, B, C should be as short as possible.
- (6) The point D at which the wiring to CIN filter is divided should be near the terminal of shunt resistor. NU, NV, NW terminals should be connected at near NU, NV, NW terminals.
- (7) All capacitors should be mounted as close to the terminals as possible. (C1: good temperature, frequency characteristic electrolytic type and C2:0.01 μ -2 μ F, good temperature, frequency and DC bias characteristic ceramic type are recommended.)
- (8) Input drive is High-active type. There is a minimum 3.3k Ω pull-down resistor in the input circuit of IC. To prevent malfunction, the wiring of each input should be as short as possible. When using RC coupling circuit, make sure the input signal level meet the turn-on and turn-off threshold voltage.
- (9) Thanks to built-in HVIC, direct coupling to MCU without any optocoupler or transformer isolation is possible.
- (10) Fo output is open drain type. It should be pulled up to MCU or control power supply (e.g. 5V,15V) by a resistor that makes I_{FO} up to 1mA. (I_{FO} is estimated roughly by the formula of control power supply voltage divided by pull-up resistance. In the case of pulled up to 5V, 10k Ω (5k Ω or more) is recommended.)
- (11) Two V_{NC} terminals are connected inside DIPIM, please connect either one to the 15V power supply GND outside and leave another one open.
- (12) If high frequency noise superimposed to the control supply line, IC malfunction might happen and cause DIPIPM erroneous operation. To avoid such problem, line ripple voltage should meet $dV/dt \leq \pm 1V/\mu s$, $V_{ripple} \leq 2Vp-p$.

The DIIPIM signal input section integrates a 3.3kΩ(min) pull-down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at input terminal.

DIPIPM

NU, NV, NW should be connected each other at near terminals.

Wiring Inductance should be less than 10nH.
 { Inductance of a copper pattern with length=17mm, width=3mm is about 10nH. }

NU
NV
NW

Shunt resistor

N1

GND wiring from V_{NC} should be connected close to the terminal of shunt resistor.

V_{NC}

DIPIPM

Each wiring Inductance should be less than 10nH.
 { Inductance of a copper pattern with length=17mm, width=3mm is about 10nH. }

NU
NV
NW

Shunt resistors

N1

GND wiring from V_{NC} should be connected close to the terminal of shunt resistor.

V_{NC}

The schematic diagram illustrates the internal components of the DIP1PM power module. It features a Drive circuit with P-side and N-side MOSFETs, a Protection circuit with a shunt resistor (N1), and an External protection circuit with a shunt resistor (N1) and a comparator (Open collector output type). The module is connected to a 5V supply and ground.

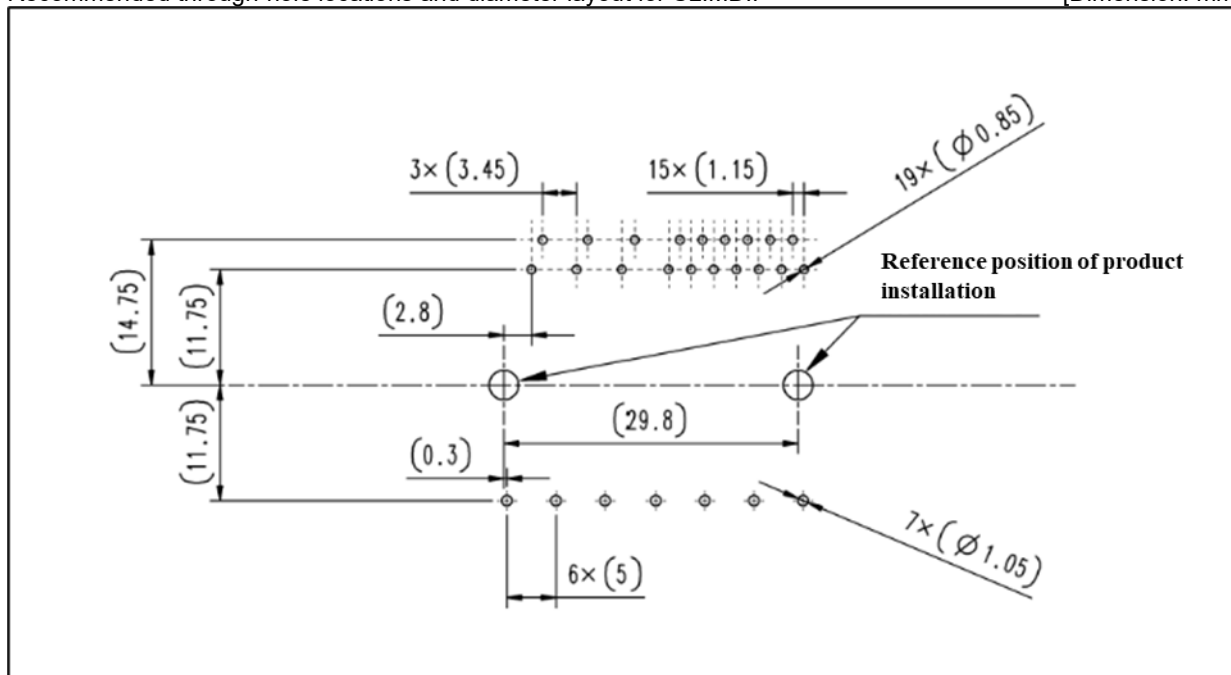
- (1) It is necessary to set the time constant $R_C C_f$ of external comparator input so that IGBT stop within $2\mu s$ when short circuit occurs. SC interrupting time might vary with the wiring pattern, comparator speed and so on.
- (2) The threshold voltage V_{ref} should be set up the same rating of short circuit trip level ($V_{sc(ref)}$ typ. 0.48V).
- (3) Select the external shunt resistance so that SC trip-level is less than specified maximum value.
- (4) To avoid malfunction, the wiring A, B, C should be as short as possible.
- (5) The point D at which the wiring to comparator is divided should be near the terminal of shunt resistor.
- (6) OR output high level should be over 0.505V (=maximum $V_{sc(ref)}$).
- (7) GND of Comparator, V_{ref} circuit and C_f should be not connected to noisy power GND but to control GND wiring.

SLIMDIP-WTRANSFER MOLDING TYPE
INSULATED TYPE

Fig. 10 (Reference Figure) PCB Through-hole Pattern

Recommended through-hole locations and diameter layout for SLIMDIP

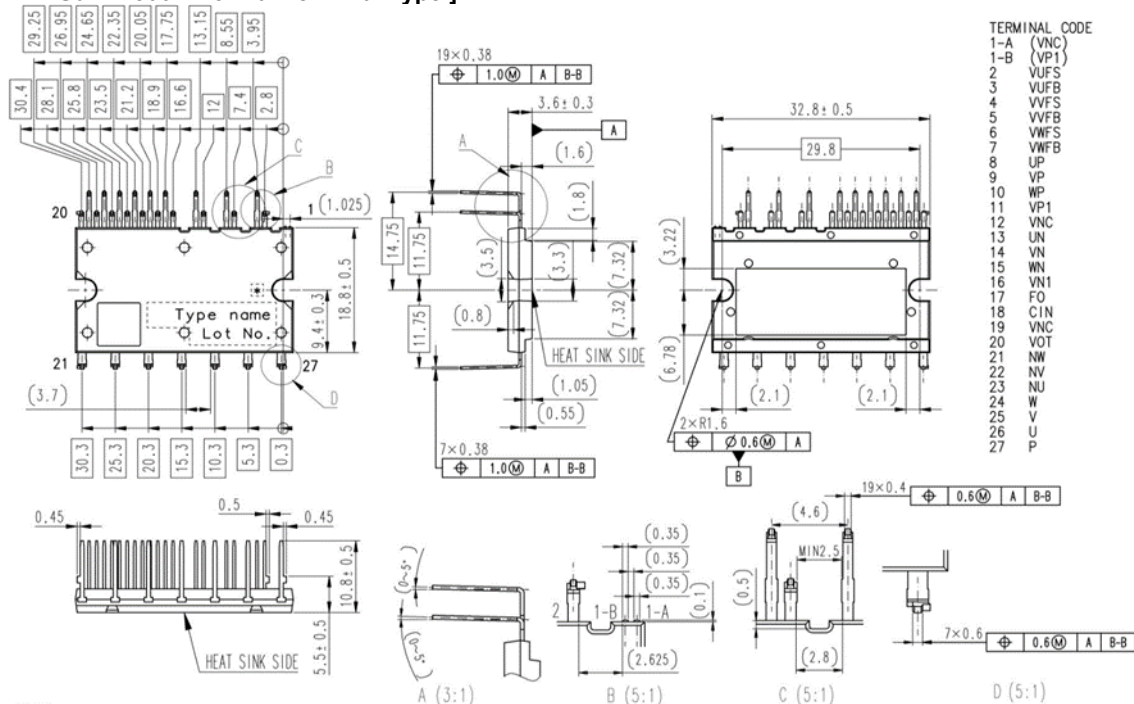
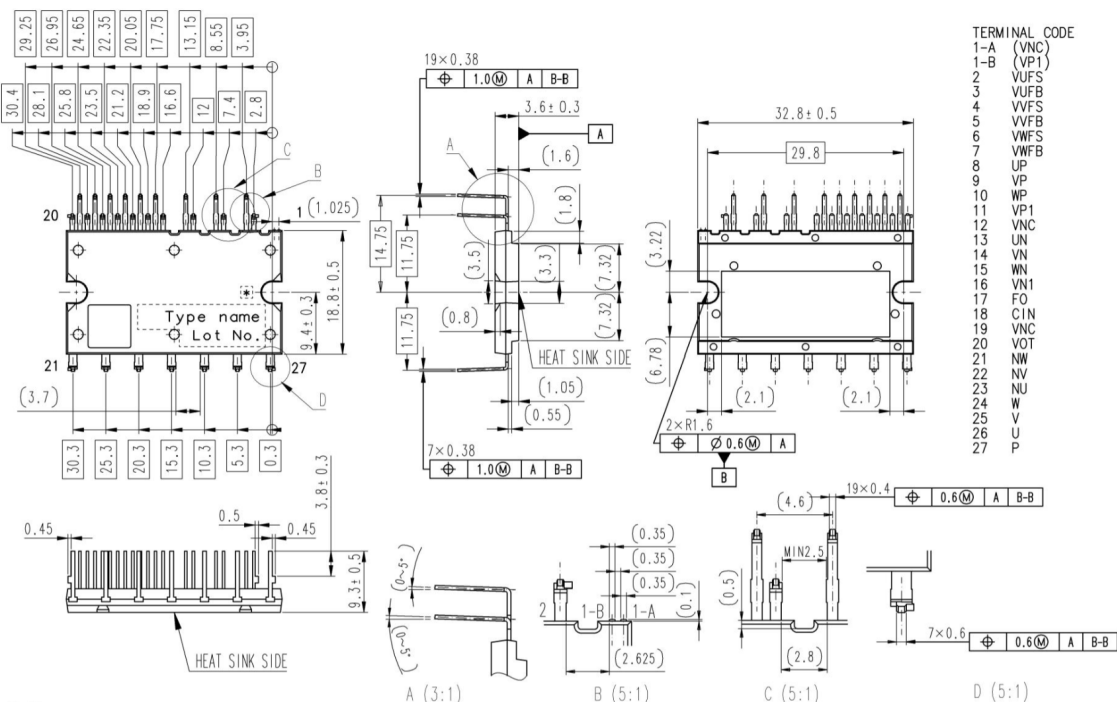
[Dimension: mm]



SLIMDIP-W**TRANSFER MOLDING TYPE
INSULATED TYPE**

Fig. 11 Package Outlines

[Dimension: mm]

[SLIMDIP-W Suffix:500 : Normal Terminal Type]**[SLIMDIP-W Suffix:505 : Short Terminal Type]**

Note: Connect only one Vnc terminal (No.12 or 19) to the system GND and leave another one open.

Important Notice

The information contained in this datasheet shall in no event be regarded as a guarantee of conditions or characteristics. This product has to be used within its specified maximum ratings, and is subject to customer's compliance with any applicable legal requirement, norms and standards.

Except as otherwise explicitly approved by Mitsubishi Electric Corporation in a written document signed by authorized representatives of Mitsubishi Electric Corporation, our products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.

In usage of power semiconductor, there is always the possibility that trouble may occur with them by the reliability lifetime such as Power Cycle, Thermal Cycle or others, or when used under special circumstances (e.g. condensation, high humidity, dusty, salty, highlands, environment with lots of organic matter / corrosive gas / explosive gas, or situations which terminals of semiconductor products receive strong mechanical stress). Therefore, please pay sufficient attention to such circumstances. Further, depending on the technical requirements, our semiconductor products may contain environmental regulation substances, etc. If there is necessity of detailed confirmation, please contact our nearest sales branch or distributor.

The contents or data contained in this datasheet are exclusively intended for technically trained staff. Customer's technical departments should take responsibility to evaluate the suitability of Mitsubishi Electric Corporation product for the intended application and the completeness of the product data with respect to such application. In the customer's research and development, please evaluate it not only with a single semiconductor product but also in the entire system, and judge whether it's applicable. As required, pay close attention to the safety design by installing appropriate fuse or circuit breaker between a power supply and semiconductor products to prevent secondary damage. Please also pay attention to the application note and the related technical information.

Keep safety first in your circuit designs!

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

- These materials are intended as a reference to assist our customers in the selection of the Mitsubishi Electric Semiconductor product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Mitsubishi Electric Corporation or a third party.
- Mitsubishi Electric Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.
- All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Mitsubishi Electric Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Mitsubishi Electric Corporation or an authorized Mitsubishi Electric Semiconductor product distributor for the latest product information before purchasing a product listed herein.
The information described here may contain technical inaccuracies or typographical errors. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.
Please also pay attention to information published by Mitsubishi Electric Corporation by various means, including the Mitsubishi Electric Semiconductor home page (<http://www.MitsubishiElectric.com/semiconductors/>).
- When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Mitsubishi Electric Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
- Mitsubishi Electric Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Electric Semiconductor product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
- The prior written approval of Mitsubishi Electric Corporation is necessary to reprint or reproduce in whole or in part these materials.
- If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
Any diversion or re-export contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
- Please contact Mitsubishi Electric Corporation or an authorized Mitsubishi Electric Semiconductor product distributor for further details on these materials or the products contained therein.